

FEATURES

Complementary Type The NPN Transistor
MMBT3904 is Recommended
Epitaxial Planar Die Construction



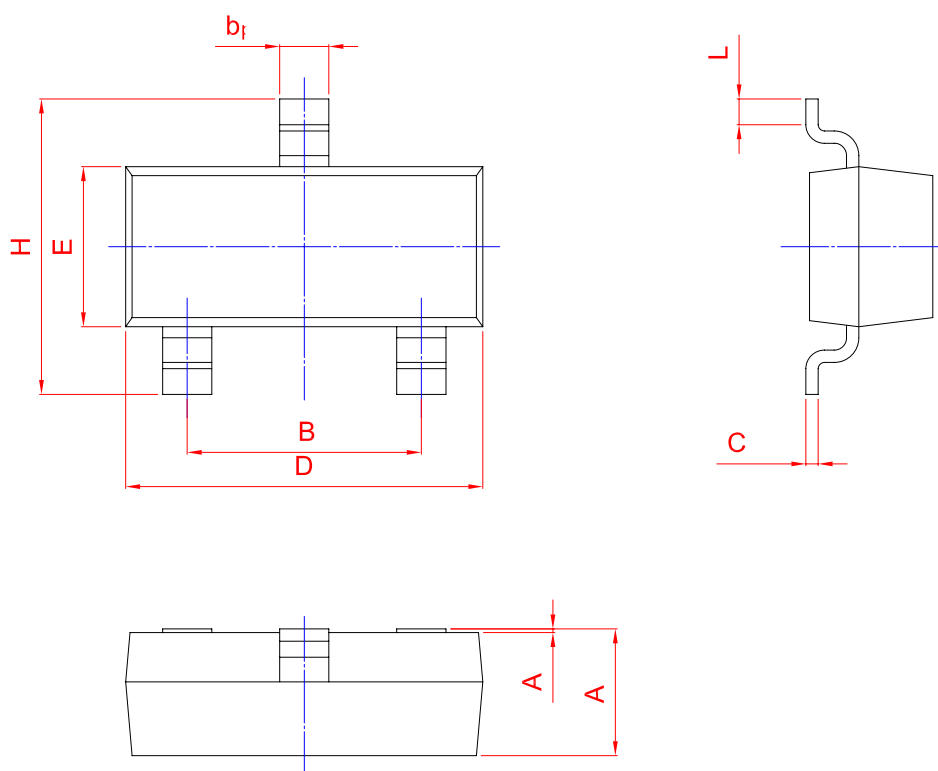
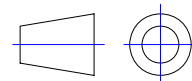
MARKING: 2A

MAXIMUM RATINGS ($T_a=25$ unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|-----------|----------------------------------------|------------|------|
| V_{CBO} | Collector-Base Voltage | -40 | V |
| V_{CEO} | Collector-Emitter Voltage | -40 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current | -200 | mA |
| P_C | Total Device Dissipation | 200 | mW |
| R_{JA} | Thermal Resistance Junction to Ambient | 625 | /W |
| T_J | Junction Temperature | 150 | |
| T_{stg} | Storage Temperature | -55 ~ +150 | |

ELECTRICAL CHARACTERISTICS ($T_a=25$ unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Max | Unit |
|----------------------------------|---------------|-----------------------|-----|-----|------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=-10\mu A, I_E=0$ | -40 | | V |



| UNIT | A | | b_p | C | D | E | H_E | A_1 | L_p |
|------|------|--|-------|------|------|------|-------|-------|-------|
| mm | 1.40 | | 0.50 | 0.19 | 3.10 | 1.65 | 3.00 | 0.100 | 0.50 |
| | 0.95 | | 0.35 | 0.08 | 2.70 | 1.20 | 2.20 | 0.013 | 0.20 |